

IGBT³ Chip

FEATURES:

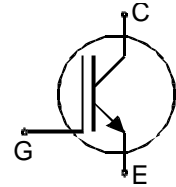
- 600V Trench & Field Stop technology
- low $V_{CE(sat)}$
- low turn-off losses
- short tail current
- positive temperature coefficient
- easy paralleling

This chip is used for:

- power module
- discrete components

Applications:

- drives



Chip Type	V_{CE}	I_{Cn}	Die Size	Package	Ordering Code
SIGC28T60	600V	50A	6.57 x 4.2 mm ²	sawn on foil	Q67050- A4337-A101

MECHANICAL PARAMETER:

Raster size	6.57 x 4.2	mm ²
Emitter pad size	2.166 x 3.401 2.432 x 3.401	
Gate pad size	0.817 x 1.52	
Area total / active	27.6 / 20	mm ²
Thickness	70	µm
Wafer size	150	mm
Flat position	90	deg
Max. possible chips per wafer	457 pcs	
Passivation frontside	Photoimide	
Emitter metallization	3200 nm AlSiCu	
Collector metallization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, <500µm	
Reject ink dot size	Ø 0.65mm ; max 1.2mm	
Recommended storage environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	

MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_j=25\text{ °C}$	V_{CE}	600	V
DC collector current, limited by T_{jmax}	I_C	¹⁾	A
Pulsed collector current, t_p limited by T_{jmax}	I_{cpuls}	150	A
Gate emitter voltage	V_{GE}	± 20	V
Operating junction and storage temperature	T_j, T_{stg}	-40 ... +175	°C
SC data, $V_{GE} = 15V, V_{CC} = 360V, T_{vj} = 150\text{ °C}$	t_p	5	μs

¹⁾ depending on thermal properties of assembly

STATIC CHARACTERISTICS (tested on chip), $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=4mA$	600			V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=50A$	1.05	1.45	1.85	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=800\mu A, V_{GE}=V_{CE}$	tbd	5.8	tbd	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600V, V_{GE}=0V$			140	μA
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=20V$			600	nA
Integrated gate resistor	R_{Gint}			none		Ω

ELECTRICAL CHARACTERISTICS (verified by design/characterization):

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	C_{iss}	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1MHz$		tbd		nF
Output capacitance	C_{oss}			tbd		
Reverse transfer capacitance	C_{riss}			tbd		

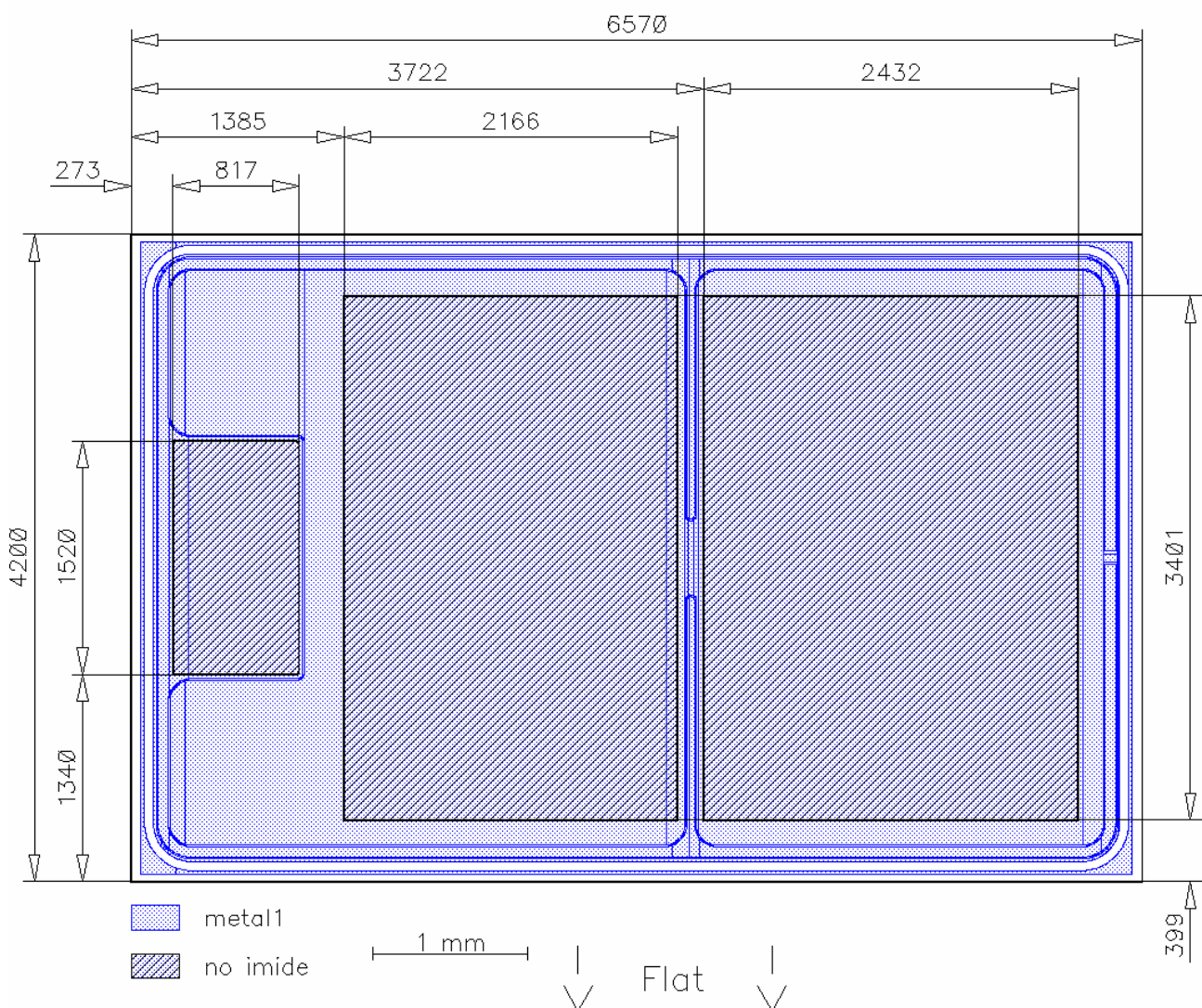
SWITCHING CHARACTERISTICS (verified by design/characterization), inductive load

Parameter	Symbol	Conditions	Value ²⁾			Unit
			min.	typ.	max.	
Turn-on delay time	$t_{d(on)}$	$T_j=125\text{ °C}$ $V_{CC}=300V,$ $I_C=50A,$ $V_{GE}=-15/15V,$ $R_G=tb d\Omega$		tbd		ns
Rise time	t_r			tbd		
Turn-off delay time	$t_{d(off)}$			tbd		
Fall time	t_f			tbd		

²⁾ values also influenced by parasitic L- and C- in measurement and package.

CHIP DRAWING:

Die-Size 6570 um x 4200 um



FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet	tbd	
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DESCRIPTION:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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